**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an LFPAK33 package using Trench MOSFET technology.

This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

## 3. Applications

- · Reverse polarity protection
- Power management
- · High-side load switch
- Motor drive

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-60	V
$V_{GS}$	gate-source voltage		[1]	-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 25 °C		-	-	-27	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C		-	-	99	W
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -7 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	48	61	mΩ

[1]  $V_{GS} = -20 \text{ V/+5 V}$  according AEC-Q101 at  $T_i = 175 \text{ °C}$ ;  $V_{GS} = -20 \text{ V/+16 V}$  according AEC-Q101 at  $T_i = 150 \text{ °C}$ 



**60 V, P-channel Trench MOSFET** 

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	S 017aaa094
			LFPAK33 (SOT1210)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
BUK6M61-60P	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK6M61-60P	66160P

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-60	V
V <sub>GS</sub>	gate-source voltage		[1]	-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 25 °C		-	-27	Α
		V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 100 °C		-	-17	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-108	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C		-	99	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode		<u>'</u>			
Is	source current	T <sub>mb</sub> = 25 °C		-	-27	А
I <sub>SM</sub>	peak source current	$T_{mb}$ = 25 °C, single pulse; $t_p \le 10 \mu s$		-	-108	А
ESD maximu	m rating		'		•	'
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	800	V
Avalanche ru	iggedness				'	'
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{sup} \le -60 \text{ V}; V_{GS} = -10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; I_D = -19.5 \text{ A}; unclamped$	[3]	-	36	mJ
		$V_{sup} \le -60 \text{ V}; V_{GS} = -10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; I_D = -4.6 \text{ A}; unclamped$	[3]	-	142	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$T_{j(init)} = 25  ^{\circ}C$	[3]	-	-19.5	А

 $V_{GS}$  = -20 V/+5 V according AEC-Q101 at  $T_j$  = 175 °C;  $V_{GS}$  = -20 V/+16 V according AEC-Q101 at  $T_j$  = 150 °C Measured between all pins.

Protected by 100% test

#### 60 V, P-channel Trench MOSFET

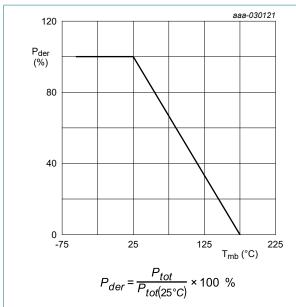


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

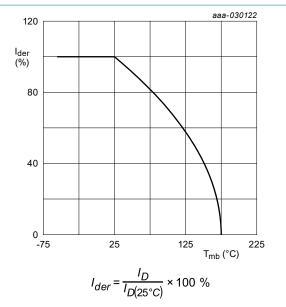


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

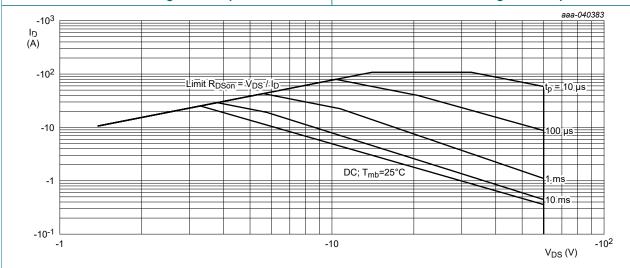


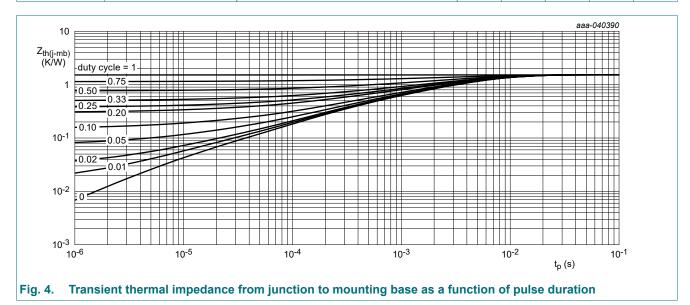
Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base		-	1.38	1.52	K/W



**60 V, P-channel Trench MOSFET** 

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-1.5	-2	-3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		V <sub>DS</sub> = -60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
$R_{DSon}$	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	48	61	mΩ
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -7 A; T <sub>j</sub> = 175 °C	-	100	130	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -6 A; T <sub>j</sub> = 25 °C	-	62	93	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -4 A; $T_{j}$ = 25 °C	-	65	-	S
$R_G$	gate resistance	f = 1 MHz	-	12	-	Ω
Dynamic ch	naracteristics		'	-		
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -30 \text{ V}; I_D = -7 \text{ A}; V_{GS} = -10 \text{ V};$	-	19	29	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	3.6	-	nC
$Q_{GD}$	gate-drain charge		-	4.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1060	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	85	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	49	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -30 \text{ V}; I_D = -7 \text{ A}; V_{GS} = -10 \text{ V};$	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	35	-	ns
t <sub>f</sub>	fall time	1	-	144	-	ns
Source-drai	in diode		'			
V <sub>SD</sub>	source-drain voltage	$I_S = -5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = -5 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	27	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = -30 V; $T_j$ = 25 °C	-	29	-	nC

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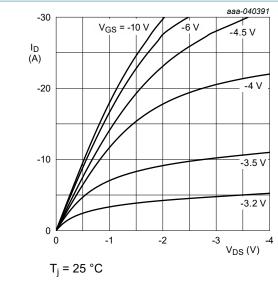


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

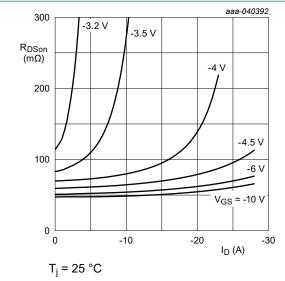


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

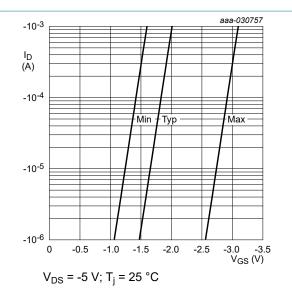


Fig. 6. Sub-threshold drain current as a function of gate-source voltage

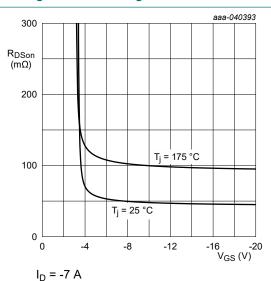


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, P-channel Trench MOSFET

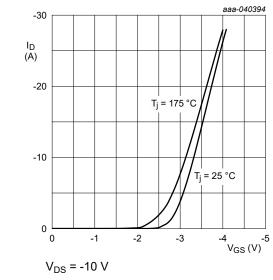


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

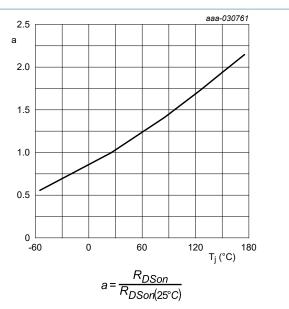


Fig. 10. Normalized drain-source on-state resistance as a function of junction temperature; typical values

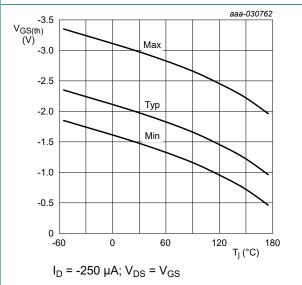


Fig. 11. Gate-source threshold voltage as a function of junction temperature

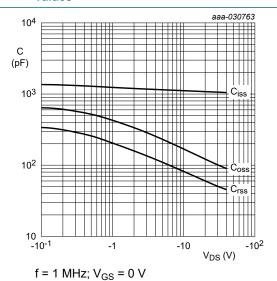


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### **60 V, P-channel Trench MOSFET**

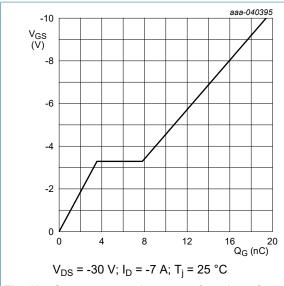


Fig. 13. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

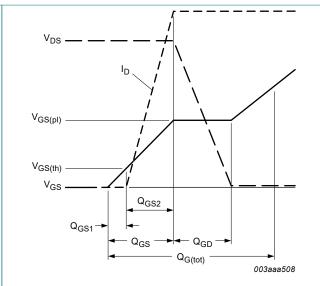


Fig. 14. Gate charge waveform definitions

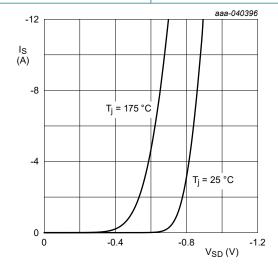
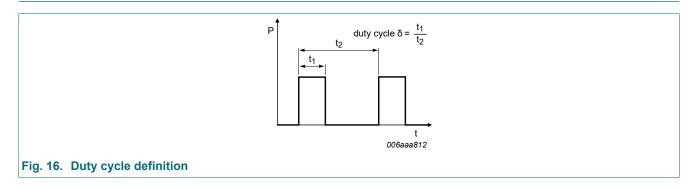


Fig. 15. Source current as a function of source-drain voltage; typical values

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## 11. Test information

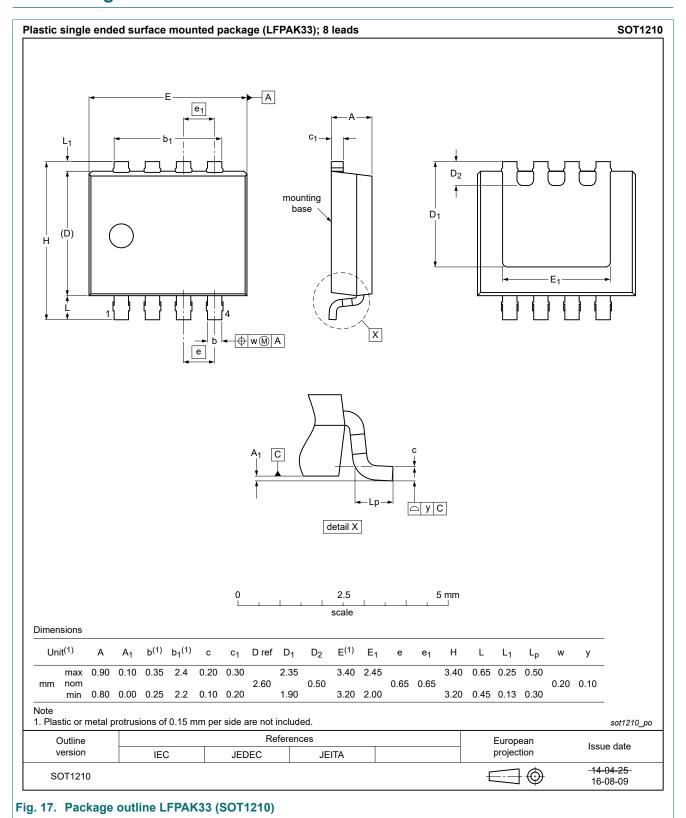


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

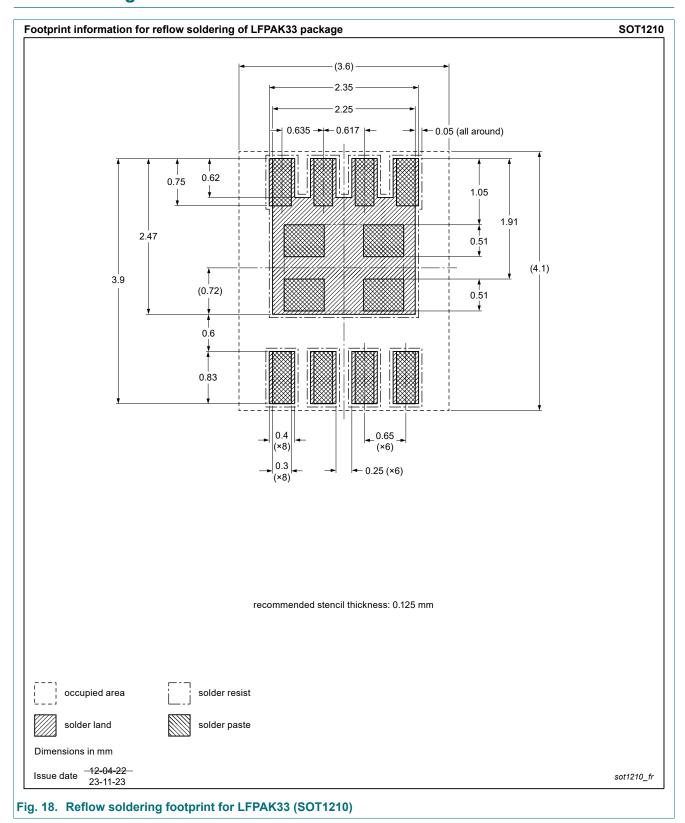
60 V, P-channel Trench MOSFET

# 12. Package outline



60 V, P-channel Trench MOSFET

# 13. Soldering



**60 V, P-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6M61-60P v.1	20240902	Product data sheet	-	-

#### 60 V, P-channel Trench MOSFET

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 2 September 2024

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